


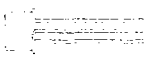





## Photo Transistors (continued)

Package	Type	Photo Sensitive Area/mm <sup>2</sup>	+/- φ	Characteristics			
				I <sub>ce</sub> / mA @ E <sub>e</sub> / mW/cm <sup>2</sup> (V <sub>CE</sub> = 5 V, λ = 950 nm)	t <sub>r</sub> / μs @ R <sub>L</sub> / kΩ (I <sub>C</sub> = 5 mA, λ = 950 nm)		
<b>Photo Transistors in Hermetically Sealed Package</b>							
	BPW76A	0.36	40°	0.4-0.6	1	3.8	0.1
	BPW76B			1.2(>0.6)			
	BPX38	0.76		>0.5	0.5	3.8	1
	BPX38-4			0.5-1.0		15	
	BPX38-5			0.8-1.6		20	
	BPX38-6			>1.25		25	
	BPW77NA	0.36	10°	7.5-15	1	3.8	0.1
	BPW77NB			20(>10)			
	S254PN	0.18		>3.0	1.5		
	BPX43	0.76	15°	>2.0	0.5	1.5	1
	BPX43-4			2.0-4.0		15	
	BPX43-5			3.2-6.3		20	
	BPX43-6			>5.0		25	
<b>Photo Darlington Transistor in Hermetically Sealed Package</b>							
	BPX99R	0.21	12°	15(>4.0)	0.3	80	0.1

## Photo Schmitt Trigger

Package	Type	+/- φ	Characteristics	
			Hysteresis E <sub>off</sub> /E <sub>on</sub> (%)	t <sub>r</sub> /t <sub>f</sub> (ns) R <sub>L</sub> =1 kΩ, V <sub>S</sub> =5 V
<b>Silicon Photo Detector with Logic Output</b>				
	TESS5400 INLINE	35°	80	100 / 20

## Photo Diodes

Package	Type	Photo Sensitive Area/mm <sup>2</sup>	+/- φ	I <sub>k</sub> / μA @ E <sub>A</sub> = 1 klx	V <sub>0</sub> / mV	t <sub>on</sub> / μs @ R <sub>L</sub> / kΩ (I <sub>ph</sub> = 100 μA)
<b>Photo Diodes for Light Measurement Applications</b>						
	BPW20R	7.5	50°	61(>20)	500	3.5 <sup>1)</sup>
	BPW21R (with V(λ) filter)			9(>4.5)	450	